

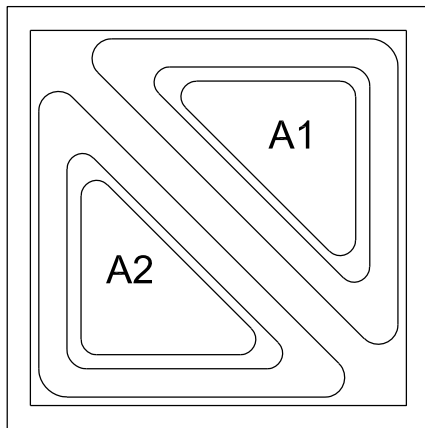
PROCESS CPD30V
Dual Switching Diode
Dual, Common Cathode,
High Speed Switching Diode Chip



PROCESS DETAILS

Die Size	15.4 x 15.4 MILS
Die Thickness	7.1 MILS
Anode 1 Bonding Pad Area	5.9 x 5.9 x 8.3 MILS
Anode 2 Bonding Pad Area	5.9 x 5.9 x 8.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 10,000Å

GEOMETRY



BACKSIDE COMMON CATHODE R0

GROSS DIE PER 4 INCH WAFER

46,200

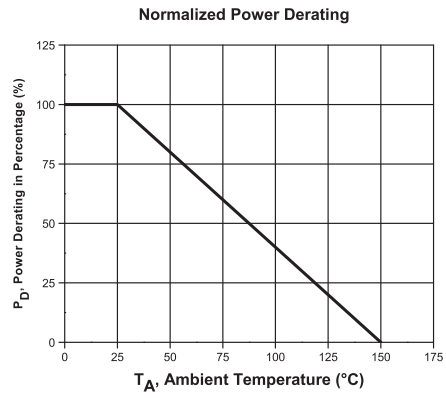
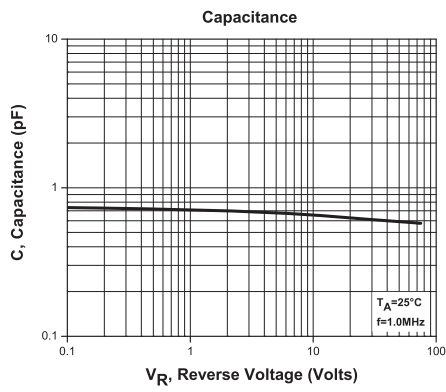
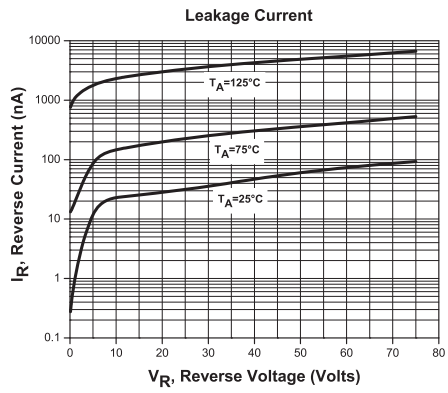
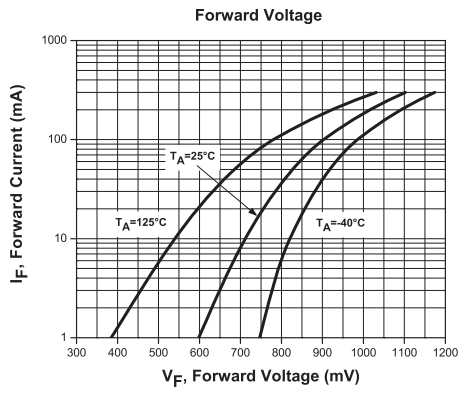
PRINCIPAL DEVICE TYPE

CMLD2838

R2 (6-October 2011)

PROCESS CPD30V

Typical Electrical Characteristics



R2 (6-October 2011)